

GSDBAS21 Series

Switching Diode

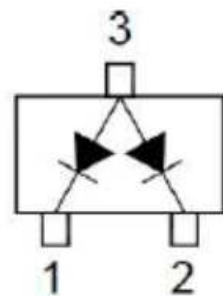
Product Description

Switching Diode 400mA / 250V

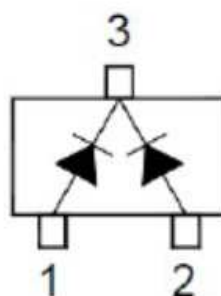
Features

- Low forward voltage
- Fast reverse recovery time
- Halogen/Lead(Pb)-Free

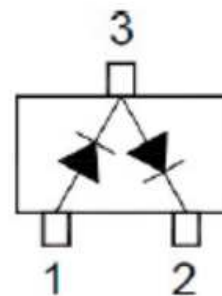
Packages



GSDBAS21A



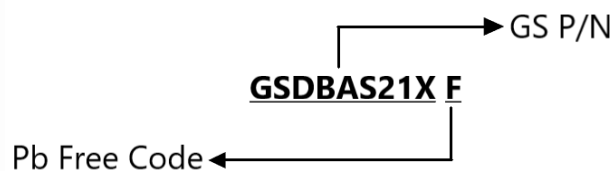
GSDBAS21C



GSDBAS21S

SOT- 23

Ordering Information



Part Number	Package	Quantity
GSDBAS21AF	SOT- 23	3000 PCS
GSDBAS21CF	SOT- 23	3000 PCS
GSDBAS21SF	SOT- 23	3000 PCS

Absolute Maximum Ratings

(T_A=25°C Unless otherwise noted)

Symbol	Conditions	Value	Unit
V _{RRM}	Peak Repetitive Reverse Voltage	250	V
V _R	Reverse Voltage	200	V
I _F	Forward Current	400	mA
I _{FSM}	Peak Forward Surge Current, t = 1μs t = 100μs	9 3	A
P _D	Total Power Dissipation	350	mW
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature Range	-55 to +150	°C

Electrical Characteristics

(T_A=25°C Unless otherwise noted)

Symbol	Conditions	Min	Max	Unit
V _F	Forward Voltage (I _F =100mA) (I _F =200mA)	-	1 1.25	V
V _{(BR)R}	Reverse BreVoltage , I _R =100μA	250	-	V
I _R	Reverse Current , (V _R =200V, T _J =25°C)	-	0.1	μA
	Reverse Current , (V _R =200V, T _J =150°C)	-	100	
C _d	Diode Capacitance (V _R =0V, f=1.0MHz),	-	5	pF
T _{rr}	Reverse Recovery Time I _F = I _R =30mA, I _{rr} =0.1* I _R , R _L =100Ω	-	50	ns

Typical Characteristics

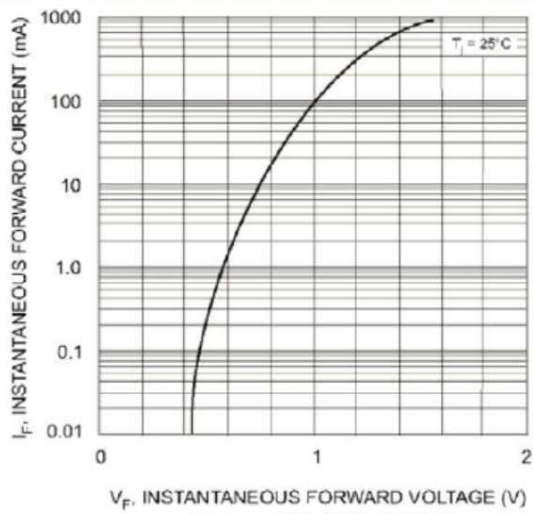


Fig. 1 Forward Characteristics

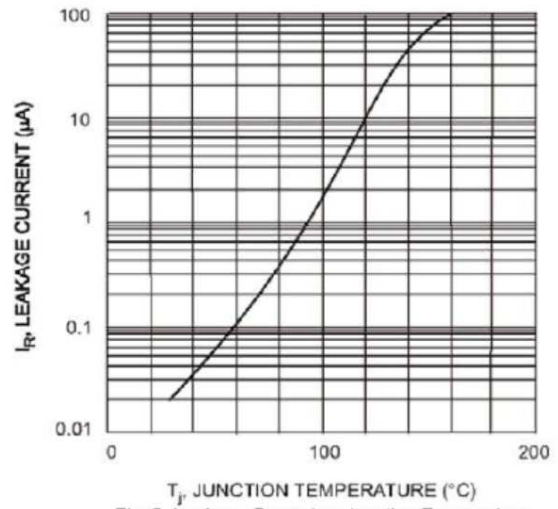
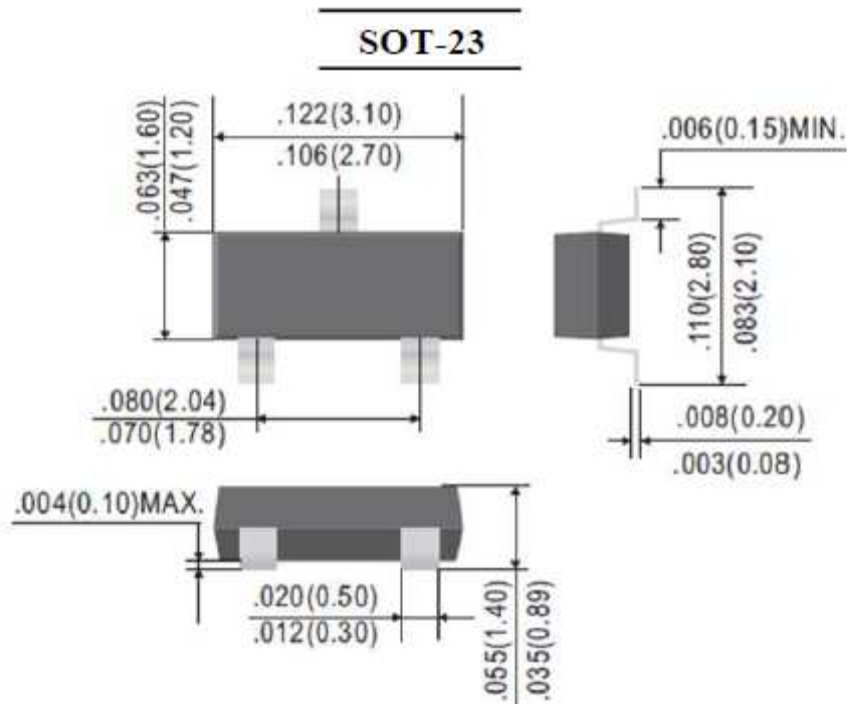


Fig. 2 Leakage Current vs Junction Temperature

Package Dimension









Dimensions in inches and (millimeter)

NOTICE

Information furnished is believed to be accurate and reliable. However Globaltech Semiconductor assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties, which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Globaltech Semiconductor. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information without express written approval of Globaltech Semiconductor.

CONTACT US

GS Headquarter	
	4F.,No.43-1,Lane11,Sec.6,Minquan E.Rd Neihu District Taipei City 114, Taiwan (R.O.C)
	886-2-2657-9980
	886-2-2657-3630
	sales_twn@gs-power.com

RD Division	
	824 Bolton Drive Milpitas. CA. 95035
	1-408-457-0587